CURRENT 20 Ampere
VOLTAGE RANG 200 Volts

ASE20N20F

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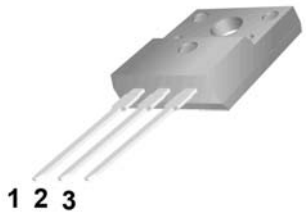
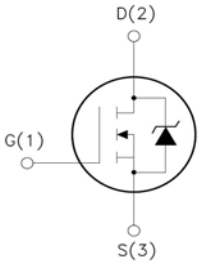
Features:

- ☐ Low Intrinsic Capacitances
- ☐ Excellent Switching Characteristics
- ☐ Extended Safe Operating Area
- ☐ Unrivalled Gate Charge :Qg= 45nC (Typ.)
- ☐ BVDSS=200V,ID=20A
- ☐ $R_{DS(on)}$:0.18 Ω (Max) @VG=10V
- ☐ 100% Avalanche

TO-220F





1.Gate (G)
2.Drain (D)
3.Source (S)

Absolute Maximum Ratings (Ta=25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain-Source Voltage		200	V
I_D	Drain Current	T_j=25℃	20	A
		T_j=100℃	11.9	
$V_{GS(TH)}$	Gate Threshold Voltage		±30	V
E_{AS}	Single Pulse Avalanche Energy (note1)		250	mJ
I_{AR}	Avalanche Current (note2)		18	A
P_D	Power Dissipation (Tj=25℃)		46	W
T_j	Junction Temperature(Max)		150	℃
T_{stg}	Storage Temperature		-55~+150	℃
TL	Maximum lead temperature for soldering purpose,1/8” from case for 5 seconds		300	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance,Junction to Case	-	3.1	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	-	62.5	℃/W

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Electrical Characteristics (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA，V_{GS}=0	200	-	-	V
△BVDSS/△TJ	Breakdown Voltage Temperature Coefficient	I_D=250μA ,Reference to 25℃	-	0.25	-	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=200V, V_{GS}=0V	-	-	1	μA
		V_{DS}=160V, Tj=125℃			10	
I_{GSSF}	Gate-body leakage Current, Forward	V_{GS}=+30V, V_{DS}=0V	-	-	100	nA
I_{GSSR}	Gate-body leakage Current, Reverse	V_{GS}=-30V, V_{DS}=0V	-	-	-100	
On Characteristics						
$V_{GS(TH)}$	Date Threshold Voltage	I_D=250μA,V_{DS}=V_{GS}	2	-	4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	I_D=20A,V_{GS}=10V	-	-	0.18	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	V_{DS}=25V，V_{GS}=0，f=1.0MHz	-	1250	1380	pF
Coss	Output Capacitance		-	200	260	
Crss	Reverse Transfer Capacitance		-	25	33	
Switching Characteristics						
Td(on)	Turn-On Delay Time	V_{DD}=100V，I_D=20A R_G=25Ω (Note 3,4)	-	16	40	ns
Tr	Turn-On Rise Time		-	133	275	
Td(off)	Turn-Off Delay Time		-	38	85	
Tf	Turn-Off Rise Time		-	62	135	
Qg	Total Gate Charge	V_{DS}=160V,V_{GS}=10V，I_D=20A (Note 3,4)	-	20	26	nC
Qgs	Gate-Source Charge		-	5.6	-	
Qgd	Gate-Drain Charge		-	10	-	
Drain-Source Diode Characteristics and Maximum Ratings						
Is	Max. Diode Forward Current	-	-	-	20	A
I_{SM}	Max. Pulsed Forward Current	-	-	-	72	
V_{SD}	Diode Forward Voltage	I_D=20A	-	-	1.5	V
Trr	Reverse Recovery Time	I_S=20A,V_{GS} =0V diF/dt=100A/μs (Note3)	-	158	-	nS
Qrr	Reverse Recovery Charge		-	1.0	-	μC

Notes : 1, L=3.0mH, IAS=18A, VDD=50V, RG=25 Ω, Starting TJ =25°C
2, Repetitive Rating : Pulse width limited by maximum junction temperature
3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
4, Essentially Independent of Operating Temperature

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Typical Characteristics

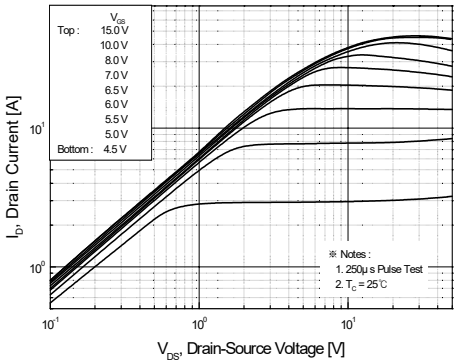

Figure 1. On-Region Characteristics

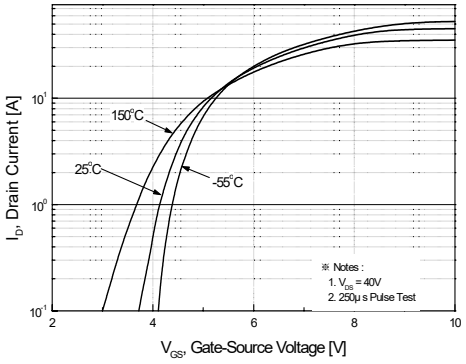

Figure 2. Transfer Characteristics

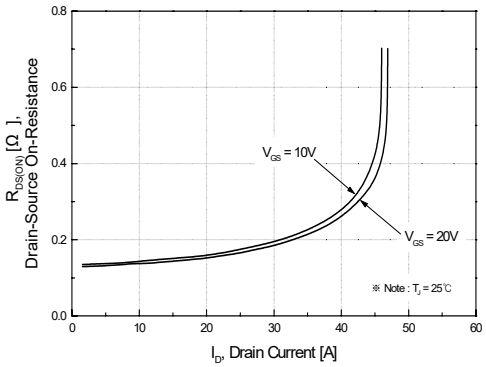

Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

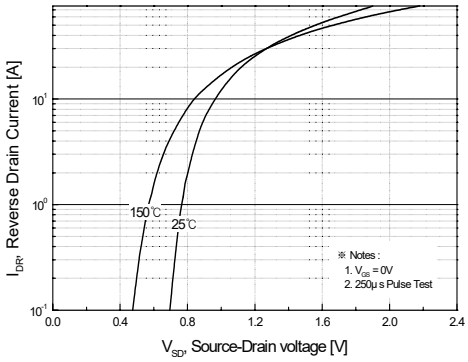

Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

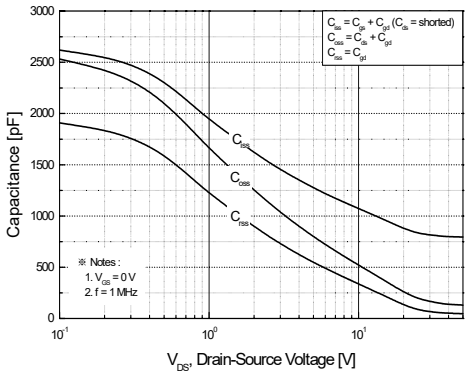

Figure 5. Capacitance Characteristics

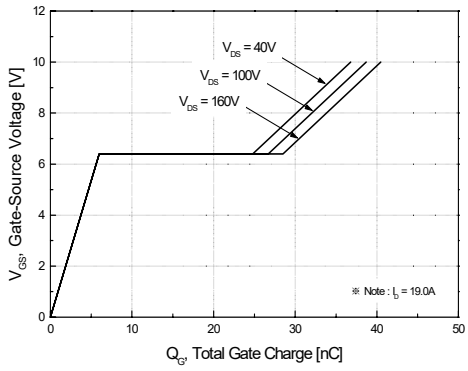

Figure 6. Gate Charge Characteristics

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Typical Characteristics (Continued)

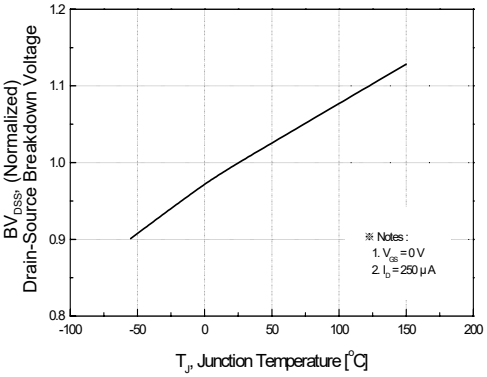

Figure 7. Breakdown Voltage Variation vs Temperature

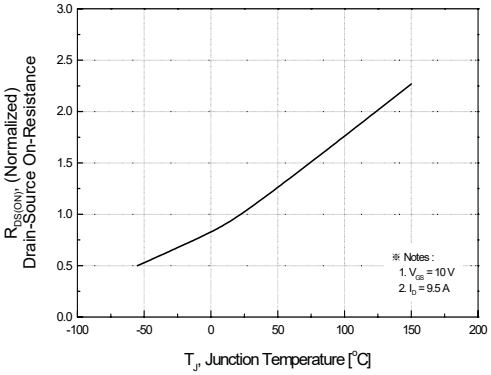

Figure 8. On-Resistance Variation vs Temperature

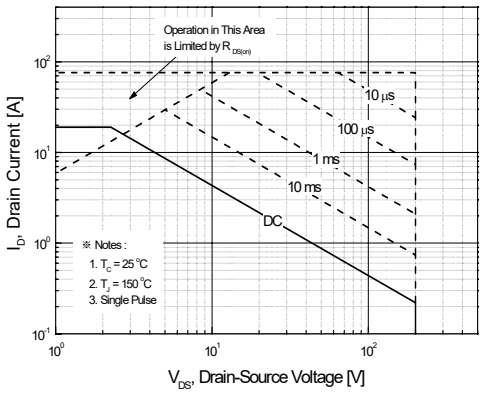

Figure 9-2. Maximum Safe Operating Area

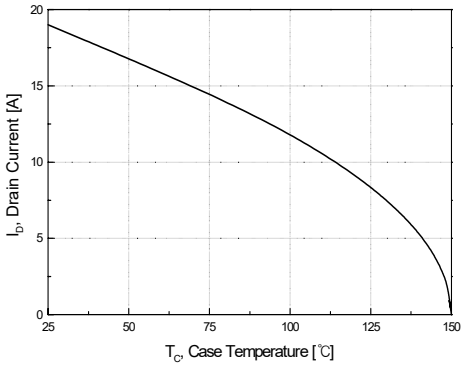

Figure 10. Maximum Drain Current vs Case Temperature

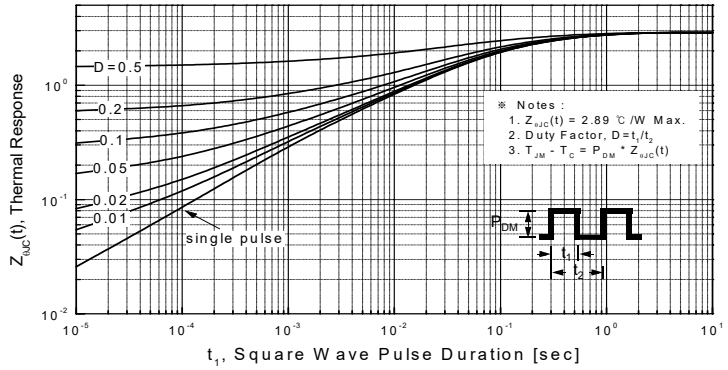

Figure 11-2. Transient Thermal Response Curve

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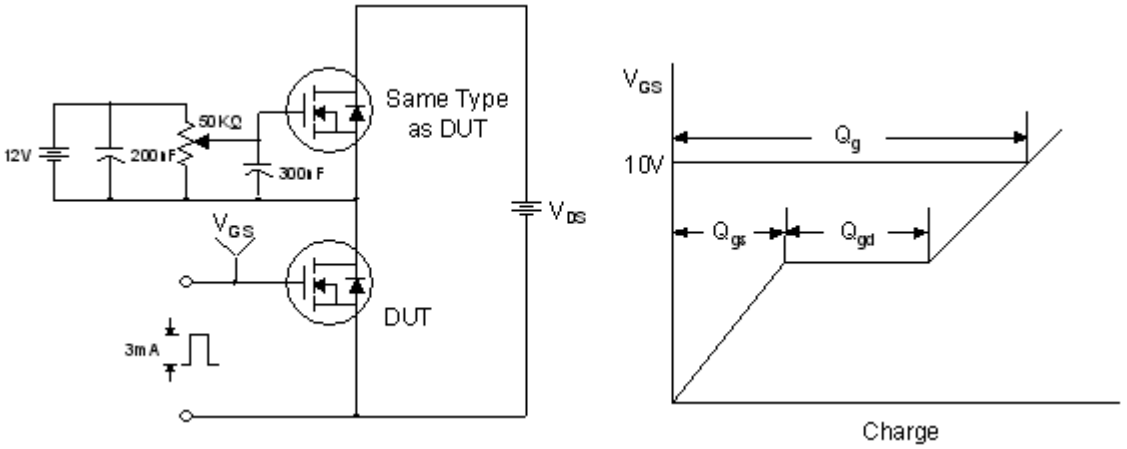
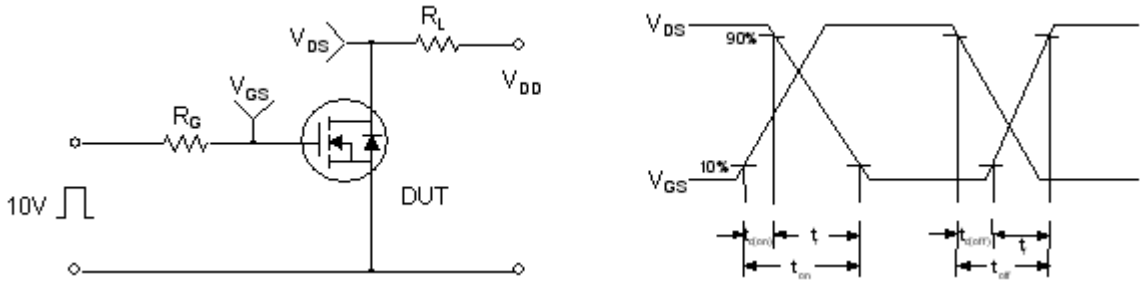
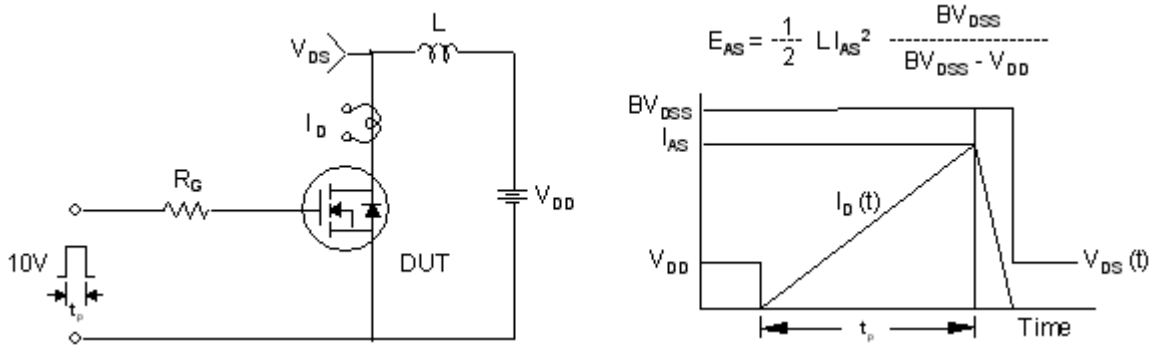
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



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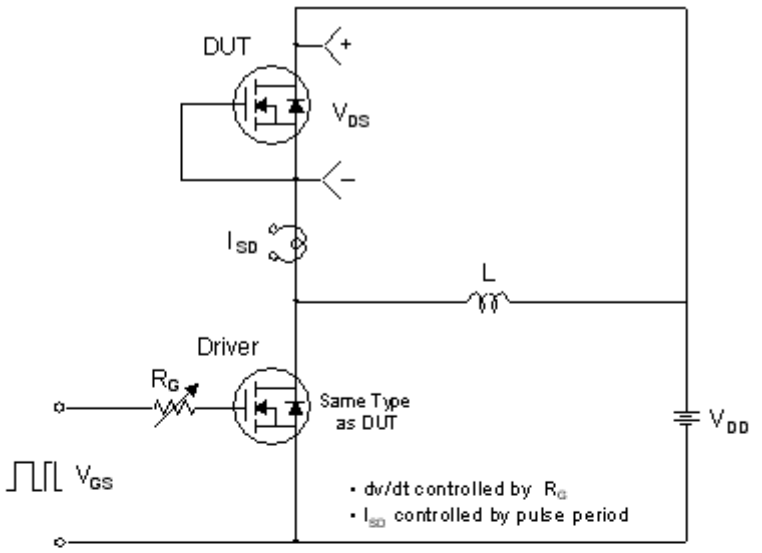
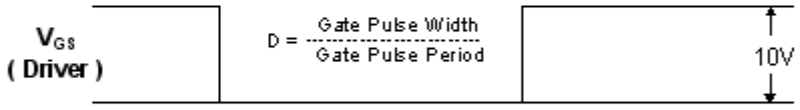
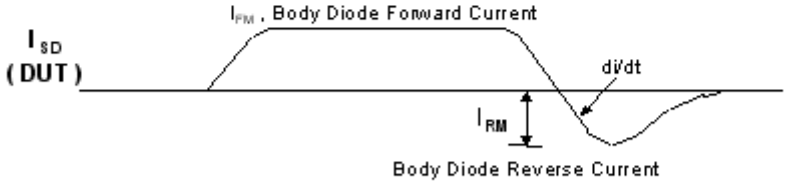
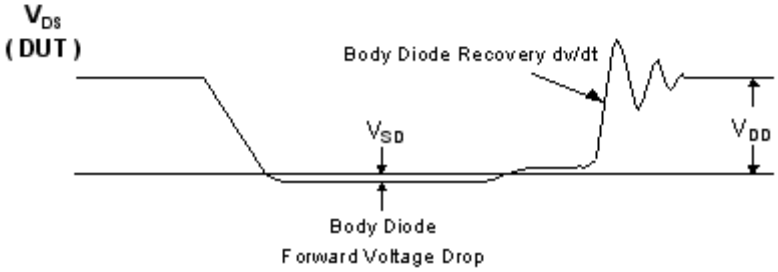
Peak Diode Recovery dv/dt Test Circuit & Waveforms









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Package Dimension

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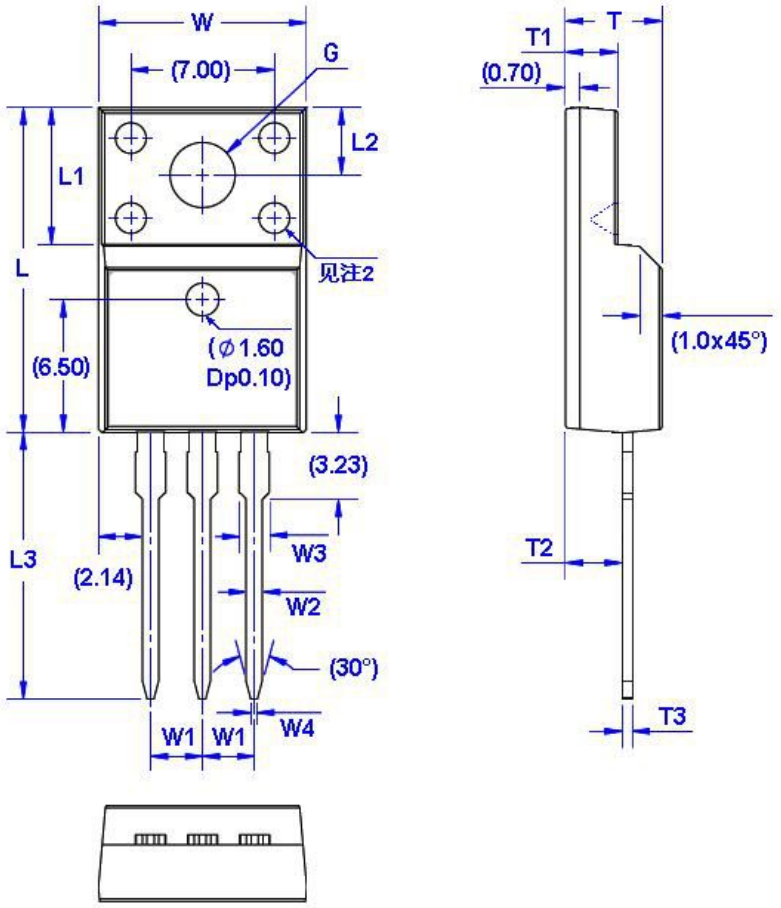
Unit: mm



符号	尺寸		符号	尺寸		符号	尺寸		符号	尺寸	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.96	10.36	W4	0.25	0.45	L3	12.78	13.18	T3	0.45	0.60
W1	2.54 (TYP)		L	15.67	16.07	T	4.50	4.90	G(Φ)	3.08	3.28
W2	0.70	0.90	L1	6.48	6.88	T1	2.34	2.74			
W3	1.24	1.47	L2	3.20	3.40	T2	2.56	2.96			